IN THE CLAIMS

A listing of the claims presented in this patent application appears below. This listing replaces all prior versions and listing of claims in this patent application.

Claims 1 – 17 (Cancelled)

18. (Previously Presented) An electret comprising:

a charged silicon oxide film;

a first insulating film formed to cover upper and side surfaces of the silicon oxide film; and

a second insulating film formed to cover a lower surface of the silicon oxide film.

19. (Previously Presented) The electret of claim 18, wherein each of the first and second insulating films is a silicon nitride film.

20. (Previously Presented) The electret of claim 18, wherein the silicon oxide film has been charged by a plasma discharge or a corona discharge.

21. (Previously Presented) An electret condenser comprising:

a fixed film having a first electrode; and

a vibrating film disposed with an air gap interposed between itself and the fixed film, wherein

the vibrating film has a multilayer structure composed of a charged silicon oxide film, a second electrode, a first insulating film, and a second insulating film,

the silicon oxide film is disposed between the first and second electrodes,

upper and side surfaces of the silicon oxide film are covered with the first insulating film, and

a lower surface of the silicon oxide film is covered with the second insulating film.

22. (Previously Presented) The electret condenser of claim 21, wherein the lower surface of the silicon oxide film is covered with the second insulating film with the second electrode interposed therebetween.

23. (Previously Presented) The electret condenser of claim 21, wherein the vibrating film is formed with a plurality of through holes each reaching the air gap and

a surface of the silicon oxide film which forms each of respective inner wall surfaces of the plurality of through holes is covered with the first insulating film.

24. (Previously Presented) The electret condenser of claim 21, wherein each of the first and second insulating films is a silicon nitride film.

25. (Previously Presented) The electret condenser of claim 21, wherein each of the first and second electrodes is made of aluminum, an aluminum alloy, silicon, polysilicon, gold, or a refractory metal.

26. (Previously Presented) The electret condenser of claim 21, wherein an area of the second electrode is smaller than an area of the silicon oxide film.

27. (Previously Presented) The electret condenser of claim 21, wherein the silicon oxide film has been charged by a plasma discharge or a corona discharge.

28. (Currently Amended) An electret condenser comprising:

a semiconductor substrate having a region removed to leave a peripheral portion thereof; and

a vibrating film formed on the semiconductor substrate to cover the region, wherein

the vibrating film has a multilayer structure composed of a charged silicon oxide film, an electrode film, a first insulating film, and a second insulating film, and

upper and side surfaces of the silicon oxide film are covered with the first insulating film and

a lower surface of the silicon oxide film is covered with the second insulating film.

29. (Currently Amended) The electret condenser of claim 28, wherein

~~upper and side surfaces of the silicon oxide film are covered with the first insulating film and~~

[[a]] the lower surface of the silicon oxide film is covered with the second insulating film with the electrode film interposed therebetween.

30. (Previously Presented) The electret condenser of claim 28, wherein the electrode film is disposed between the semiconductor substrate and the silicon oxide film.

31. (Previously Presented) The electret condenser of claim 28, wherein each of the first and second insulating films is a silicon nitride film.

32. (Previously Presented) The electret condenser of claim 28, wherein the electrode film is formed inside the region in non-overlapping relation with the semiconductor substrate.